

SE7N70

N-Channel Enhancement-Mode MOSFET

Revision: A

General Description

This series is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics

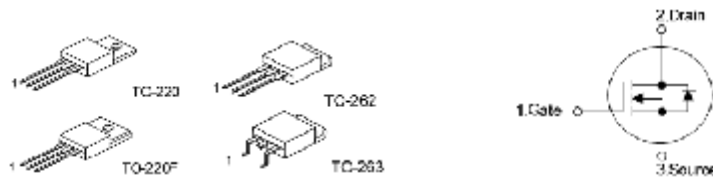
Features

For a single MOSFET

- $V_{DS} = 700V$
- $R_{DS(ON)} = 0.86\Omega @ V_{GS}=10V$

Pin configurations

See Diagram below



Absolute Maximum Ratings

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	700	V
Gate-Source Voltage		V_{GS}	± 30	V
Avalanche Current ²		I_{AR}	8	A
Drain Current	Continuous	I_D	8	A
	Pulsed		32	
Avalanche Energy Single Pulsed ³		E_{AS}	530	mJ
Peak Diode Recovery dv/dt ⁴		Dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262/TO-263	P_D	142	W
	TO-220F		48	
Operating Junction Temperature Range		T_J	-55 to 150	$^{\circ}C$

Note 1: Absolute maximum ratings are those values beyond which the device could be permanently damaged

Note 2: Repetitive Rating: Pulse width limited by maximum junction temperature

Note 3: $L=30mH, I_{AS}=4A, V_{DD}=50V, R_G=25\Omega$, starting $T_J=25^{\circ}C$

Note 4: $I_{SD}\leq 4.4A, di/dt\leq 200A/\mu s, V_{DD}\leq BV_{DSS}$, starting $T_J=25^{\circ}C$

Thermal Resistance

Symbol	Parameter	TO-220 series	TO-262/TO-263	Units
$R_{\theta JA}$	Junction to Ambient	62.5		$^{\circ}C/W$

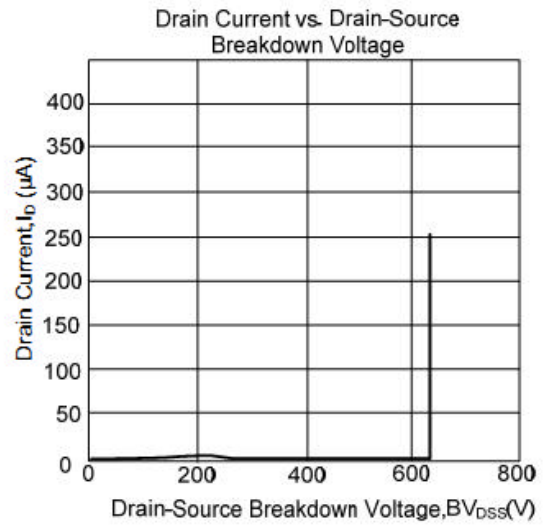
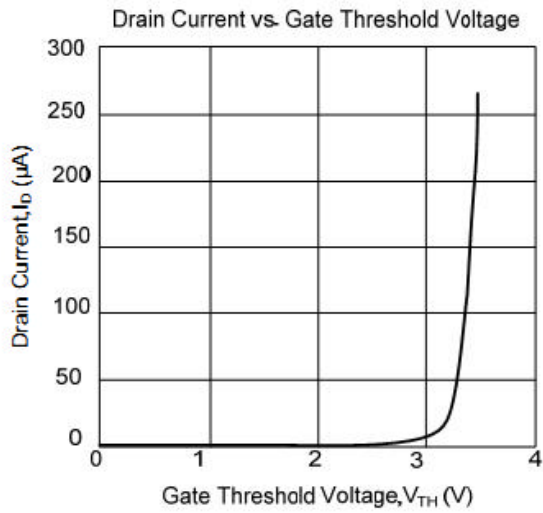
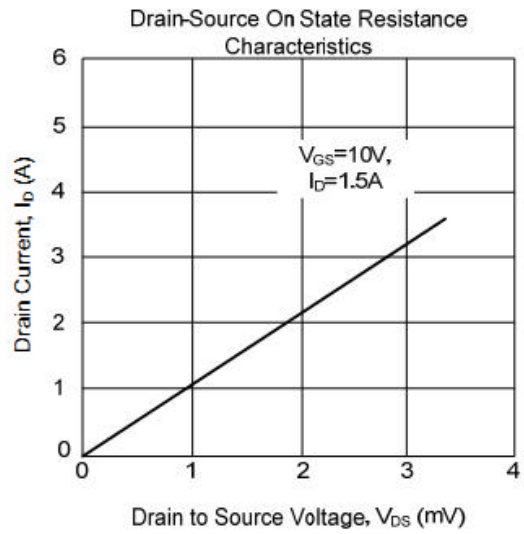
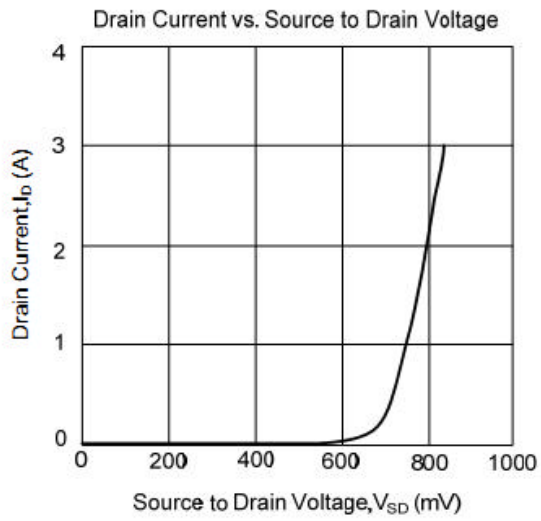
SE7N70

Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
B _V DSS	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _D =250μA,	700			V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 700V, V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =30 V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	2.0		4.0	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =3.7A		0.86	1.1	Ω
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, f=1MHz			1400	pF
C _{oss}	Output Capacitance				180	pF
C _{rss}	Reverse Transfer Capacitance			16	21	pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge ²	V _{GS} =10V, V _{DS} =480V, I _D =7.4A ^{1,2}		29	38	nC
Q _{gs}	Gate Source Charge			7		nC
Q _{gd}	Gate Drain Charge			14.5		nC
t _{d(on)}	Turn-On Delay Time	V _{DS} =300V, R _{GEN} =25Ω I _D =7.4A ^{1,2}			70	ns
t _{d(off)}	Turn-Off Delay Time				140	ns
t _{d(r)}	Turn-On Rise Time				170	ns
t _{d(f)}	Turn-Off Fall Time				130	ns
Source-Drain Diode Characteristics						
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =7.4A			1.4	V
I _S	Max Drain-Source Diode Current				6.2	A
I _{SM}	Max Pulse Drain-Source Current				24.8	A
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =7.4A		320		ns
Q _{RR}	Reverse Recovery Charge	di _F /dt=100A/μs ¹		2.4		μC

Note 1: Pulse width≤300μs, Duty cycles≤2%

Note 1: Essentially independent of operating temperature

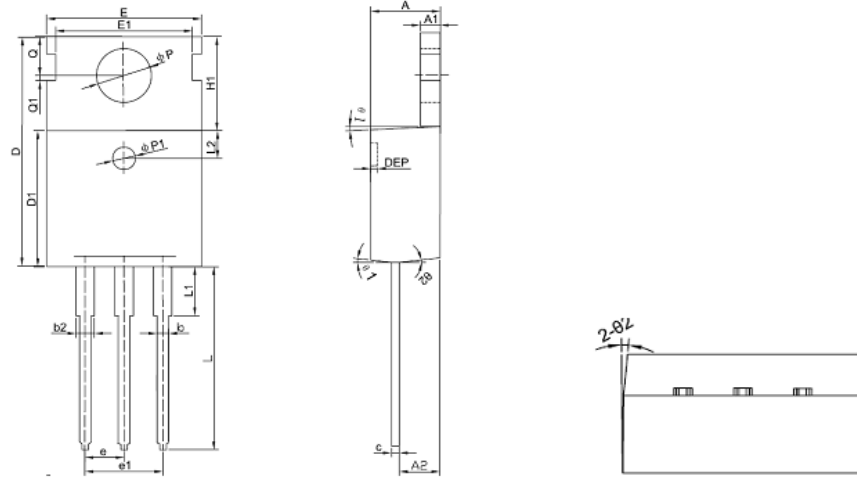
Typical Characteristics



SE7N70

Package Outline Dimension

TO-220

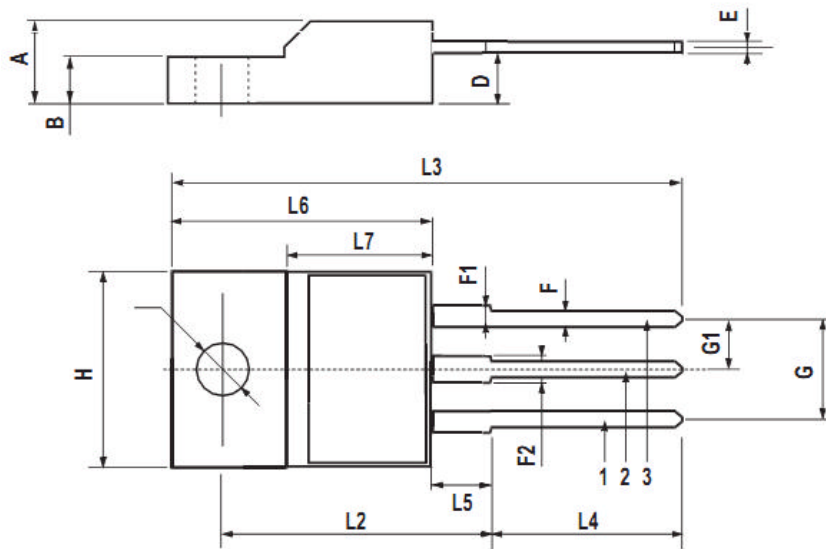


Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	4.400	4.550	4.700	0.173	0.179	0.185
A1	1.270	1.300	1.330	0.050	0.051	0.052
A2	2.590	2.690	2.790	0.102	0.106	0.110
b	0.770	-	0.900	0.030	-	0.035
b2	1.230	-	1.360	0.048	-	0.054
c	0.480	0.500	0.520	0.019	0.020	0.020
D	15.100	15.400	15.700	-	0.606	-
D1	9.000	9.100	9.200	0.354	0.358	0.362
DEP	0.050	0.285	0.520	0.002	0.011	0.020
E	10.060	10.160	10.260	0.396	0.400	0.404
E1	-	8.700	-	-	0.343	-
ØP1	1.400	1.500	1.600	0.055	0.059	0.063
e	2.54BSC			0.1BSC		
e1	5.08BSC			0.2BSC		
H1	6.100	6.300	6.500	0.240	0.248	0.256
L	12.750	12.960	13.170	0.502	0.510	0.519
L1	-	-	3.950	-	-	0.156
L2	1.85REF			0.073REF		
ØP	3.570	3.600	3.630	0.141	0.142	0.143
Q	2.730	2.800	2.870	0.107	0.110	0.113
Q1	-	0.200	-	-	0.008	-
Ø1	5 ⁰	7 ⁰	9 ⁰	5 ⁰	7 ⁰	9 ⁰
Ø2	1 ⁰	3 ⁰	5 ⁰	1 ⁰	3 ⁰	5 ⁰

SE7N70

Package Outline Dimension

TO-220F

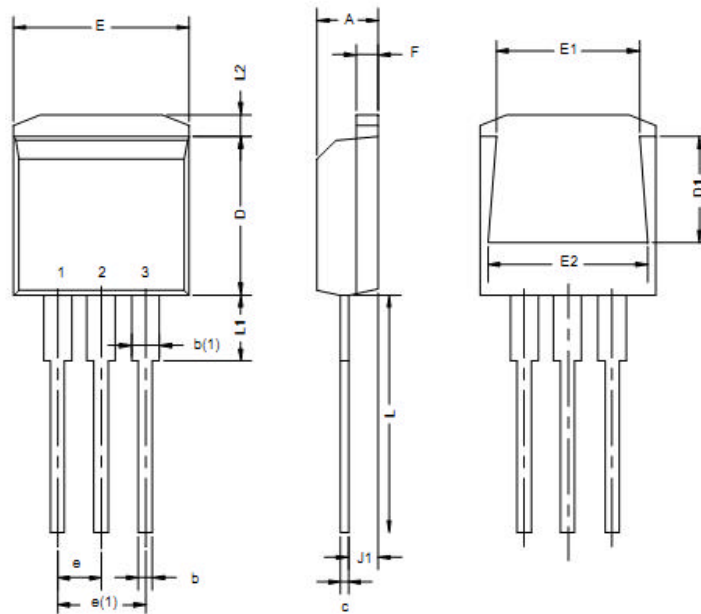


DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.5	0.045		0.067
F2	1.15		1.5	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
∅	3		3.2	0.118		0.126

SE7N70

Package Outline Dimension

TO-262



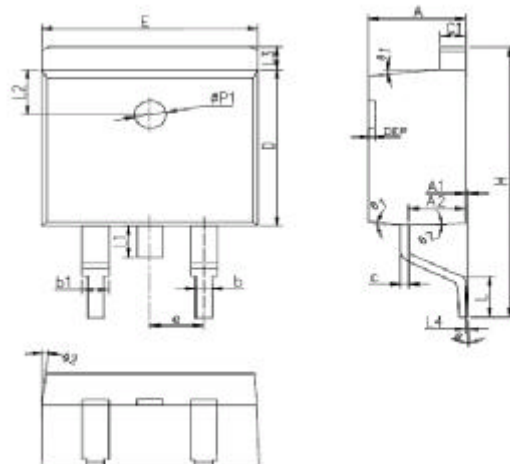
Dim	MILLIMETERS*		INCHES	
	Min	Max	Min	Max
A	4.32	4.70	0.170	0.185
b	0.64	1.00	0.025	0.039
b(1)	1.14	1.40	0.045	0.055
c	0.36	0.50	0.014	0.020
D	8.64	9.65	0.340	0.380
D1	5.59	6.10	0.220	0.240
e	2.41	2.67	0.095	0.105
e(1)	4.95	5.33	0.195	0.210
E	10.03	10.41	0.395	0.410
E1	7.87	8.64	0.310	0.340
E2	9.02	9.53	0.355	0.375
F	1.14	1.40	0.045	0.055
J1	2.41	2.79	0.095	0.110
L	13.08	14.22	0.515	0.560
L1	-	3.81	-	0.150
L2	1.02	1.40	0.040	0.055

ECN: T-02234—Rev. C, 14-Oct-02
DWG: 5855

SE7N70

Package Outline Dimension

TO-263



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	L	2.00	2.30	2.60	0.079	0.090	0.102
A1	0	0.10	0.25	0	0.004	0.010	L3	1.17	1.27	1.40	0.046	0.050	0.055
A2	2.59	2.69	2.79	0.102	0.106	0.110	L1	-	-	1.70	-	-	0.067
b	0.77	-	0.90	0.030	-	0.035	L4	0.25BSC			0.01BSC		
b1	1.23	-	1.36	0.048	-	0.052	L2	2.50REF.			0.098REF.		
c	0.34	-	0.47	0.013	-	0.019	θ	0°	-	8°	0°	-	8°
C1	1.22	-	1.32	0.048	-	0.052	$\theta 1$	5°	7°	9°	5°	7°	9°
D	8.60	8.70	8.80	0.338	0.343	0.346	$\theta 2$	1°	3°	5°	1°	3°	5°
E	10.00	10.16	10.26	0.394	0.4	0.404	DEP	0.05	0.10	0.20	0.002	0.004	0.008
e	2.54BSC			0.1BSC			$\phi P1$	1.40	1.50	1.60	0.055	0.059	0.063
H	14.70	15.10	15.50	0.579	0.594	0.610							

The SINO-IC logo is a registered trademark of ShangHai Sino-IC Microelectronics Co., Ltd.

© 2005 SINO-IC – Printed in China – All rights reserved.

SHANGHAI SINO-IC MICROELECTRONICS CO., LTD

Add: Building 3, Room 3401-03, No.200 Zhangheng Road, ZhangJiang Hi-Tech Park, Pudong,
Shanghai 201203, China

Phone: +86-21-33932402 33932403 33932405 33933508 33933608

Fax: +86-21-33932401

Email: webmaster@sino-ic.net

Website: <http://www.sino-ic.net>

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [SINO-IC](#) manufacturer:

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [BUK455-60A/B](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#) [IPS70R2K0CEAKMA1](#) [SQD23N06-31L-GE3](#)
[TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [DMN1053UCP4-7](#) [SQJ469EP-T1-GE3](#) [NTE2384](#) [DMC2700UDMQ-7](#)
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#)
[IPB80P04P405ATMA2](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [NTMC083NP10M5L](#) [BXP7N65D](#) [BXP4N65F](#) [AOL1454G](#)
[WMJ80N60C4](#) [BXP2N20L](#) [BXP2N65D](#) [BXT1150N10J](#) [BXT1700P06M](#) [TSM60NB380CP](#) [ROG](#) [RQ7L055BGTGR](#) [DMNH15H110SK3-13](#)
[SLF10N65ABV2](#) [BSO203SP](#) [BSO211P](#) [IPA60R230P6](#)